16-bit Universal Bus Driver with 3-state Outputs

# **HITACHI**

ADE-205-208 (Z) Preliminary 1st. Edition December 1997

### **Description**

This HD74ALVC16334 is a 16-bit universal bus driver is designed for 2.3 V to 3.6 V V<sub>CC</sub> operation.

Data flow from A to Y is controlled by the output enable  $(\overline{OE})$  input. The device operates in the transparent mode when the latch enable  $(\overline{LE})$  input is low. When  $\overline{LE}$  is high, the A data is latched if the clock (CLK) input is held at a high or low logic level. If  $\overline{LE}$  is high, the A data is stored in the latch/flip flop on the low to high transition of CLK. When  $\overline{OE}$  is high, the outputs are in the high impedance state.

To ensure the high impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current sinking capability of the driver.

#### **Features**

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical  $V_{OL}$  ground bounce < 0.8 V (@ $V_{CC}$  = 3.3 V, Ta = 25°C)
- Typical  $V_{OH}$  undershoot > 2.0 V (@ $V_{CC}$  = 3.3 V, Ta = 25°C)
- High output current  $\pm 24$  mA (@V<sub>CC</sub> = 3.0 V)



### **Function Table**

Inputs				Output Y
ŌĒ	LE	CLK	Α	_
Н	Х	Х	Х	Z
L	L	Χ	L	L
L	L	X	Н	Н
L	Н	<b>↑</b>	L	L
L	Н	<b>↑</b>	Н	Н
L	Н	L or H	Х	Y <sub>0</sub> *1

H : High level L : Low level

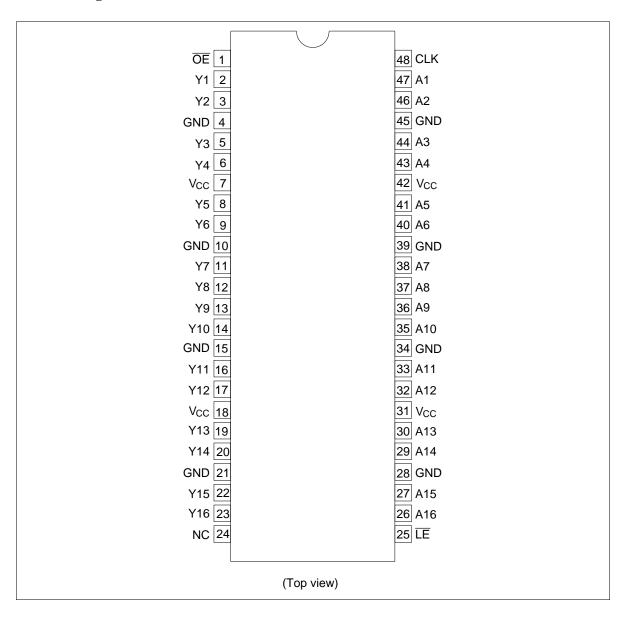
X : Immaterial

Z : High impedance

 $\uparrow$ : Low to high transition

Note: 1. Output level before the indicated steady state input conditions were established.

### **Pin Arrangement**



### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Conditions	
Supply voltage	V <sub>cc</sub>	-0.5 to 4.6	V		
Input voltage *1	Vı	-0.5 to 4.6	V		
Output voltage *1, 2	Vo	$-0.5$ to $V_{cc}$ +0.5	V		
Input clamp current	I <sub>IK</sub>	<b>-</b> 50	mA	V <sub>1</sub> < 0	
Output clamp current	I <sub>ok</sub>	±50	mA	$V_o < 0$ or $V_o > V_{cc}$	
Continuous output current	Io	±50	mA	$V_{o} = 0$ to $V_{cc}$	
V <sub>cc</sub> , GND current / pin	I <sub>CC</sub> or I <sub>GND</sub>	±100	mA		
Maximum power dissipation at Ta = 55°C (in still air) <sup>'3</sup>	P <sub>T</sub>	0.85	W	TSSOP	
Storage temperature	T <sub>stg</sub>	-65 to 150	°C		

Notes:

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

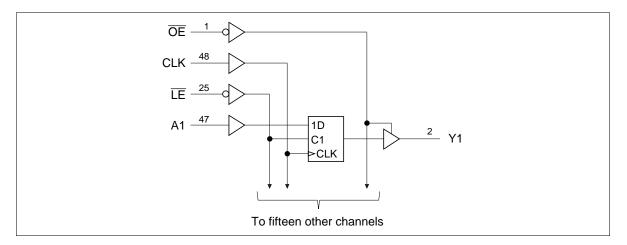
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

### **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V <sub>cc</sub>	2.3	3.6	V	
Input voltage	$V_{I}$	0	$V_{cc}$	V	
Output voltage	V <sub>o</sub>	0	$V_{cc}$	V	
High level output current	I <sub>OH</sub>	_	-12	mA	V <sub>CC</sub> = 2.3 V
		_	-12		$V_{cc} = 2.7 \text{ V}$
		_	-24		V <sub>cc</sub> = 3.0 V
Low level output current	I <sub>OL</sub>	_	12	mA	V <sub>cc</sub> = 2.3 V
		_	12		$V_{CC} = 2.7 \text{ V}$
		_	24		$V_{cc}$ = 3.0 V
Input transition rise or fall rate	Δt / Δν	0	10	ns / V	
Operating temperature	Ta	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

## Logic Diagram



## Electrical Characteristics ( $Ta = -40 \text{ to } 85^{\circ}\text{C}$ )

Item	Symbol	V <sub>cc</sub> (V)	Min	Max	Unit	Test Conditions
Input voltage	V <sub>IH</sub>	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_	=	
	V <sub>IL</sub>	2.3 to 2.7	_	0.7	_	
		2.7 to 3.6	_	0.8	_	
Output voltage	V <sub>OH</sub>	2.3 to 3.6	V <sub>cc</sub> -0.2	_	V	$I_{OH} = -100 \mu A$
		2.3	2.0	_	_	$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.3	1.7	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.7	2.2	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.4	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	_	_	$I_{OH} = -24 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V <sub>OL</sub>	2.3 to 3.6	_	0.2	_	I <sub>OL</sub> = 100 μA
		2.3	_	0.4	_	$I_{OL} = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3	_	0.7	_	$I_{OL} = 12 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.7	_	0.4	=	$I_{OL} = 12 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		3.0	_	0.55	_	$I_{OL} = 24 \text{ mA}, V_{IL} = 0.8 \text{ V}$
Input current	I <sub>IN</sub>	3.6	_	±5	μΑ	$V_{IN} = V_{CC}$ or GND
Off state output current	I <sub>oz</sub>	3.6	_	±10	μΑ	V <sub>OUT</sub> = V <sub>CC</sub> or GND
Quiescent supply current	I <sub>cc</sub>	3.6	_	40	μΑ	$V_{IN} = V_{CC}$ or GND
	$\Delta I_{CC}$	3.0 to 3.6	_	750	μА	$V_{\rm IN}$ = one input at (V <sub>CC</sub> -0.6) V, other inputs at V <sub>CC</sub> or GND

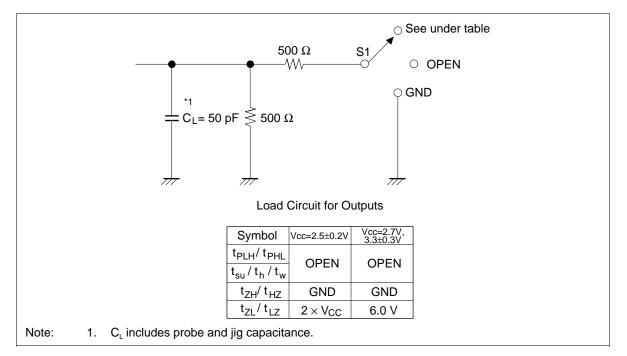
## Switching Characteristics ( $Ta = -40 \text{ to } 85^{\circ}\text{C}$ )

Item	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Maximum clock frequency	f <sub>max</sub>	2.5±0.2	150	_	_	MHz		
		2.7	150	_	_			
		3.3±0.3	150	_	_			
Propagation delay time	t <sub>PLH</sub>	2.5±0.2	1.0	_	3.7	ns	Α	Υ
	$t_{\tiny PHL}$	2.7	_	_	3.6			
		3.3±0.3	1.1	_	3.3			
		2.5±0.2	1.0	_	4.8		LE	Υ
		2.7	_	_	4.4			
		3.3±0.3	1.3	_	4.4			
		2.5±0.2	1.0	_	4.4		CLK	Υ
		2.7	_	_	4.1			
		3.3±0.3	1.0	_	4.1			
Output enable time	$t_{zH}$	2.5±0.2	1.0	_	5.4	ns	ŌĒ	Υ
	$t_{zL}$	2.7	_	_	4.6			
		3.3±0.3	1.1	_	4.6	<del></del>		
Output disable time	t <sub>HZ</sub>	2.5±0.2	1.0	_	4.1	ns	ŌĒ	Υ
	$t_{LZ}$	2.7	_	_	4.4	<del></del>		
		3.3±0.3	1.7	_	4.4			
Input capacitance	C <sub>IN</sub>	3.3	_	5.5	_	pF	Control in	nputs
		3.3	_	6.0	_	_	Data inpu	uts
Output capacitance	C <sub>o</sub>	3.3	_	8.0	_	pF	Outputs	

## **Switching Characteristics** ( $Ta = -40 \text{ to } 85^{\circ}\text{C}$ ) (cont)

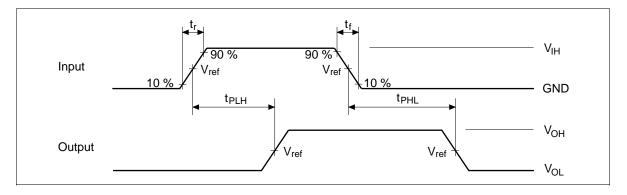
Item	Symbol	$V_{cc}$ (V)	Min	Тур	Max	Unit	FROM (Input)
Setup time	t <sub>su</sub>	2.5±0.2	1.4	_	_	ns	Data before CLK↑
		2.7	1.7	_	_	<del></del>	
		3.3±0.3	1.5	_	_		
		2.5±0.2	1.2	_	_	<del></del>	Data before <u>LE</u> ↑
		2.7	1.6	_	_	<del></del>	CLK "H"
		3.3±0.3	1.3	_	_		
		2.5±0.2	1.4	_	_	<del></del>	Data before <u>LE</u> ↑
		2.7	1.5	_	_		CLK "L"
		3.3±0.3	1.2	_	_	<del></del>	
Hold time	t <sub>h</sub>	2.5±0.2	0.9	_	_	ns	Data after CLK↑
		2.7	0.8	_	_	<del></del>	
		3.3±0.3	0.9	_	_		
		2.5±0.2	1.2	_	_		Data after <del>LE</del> ↑
		2.7	1.1	_	_		CLK "H" or "L"
		3.3±0.3	1.1	_	_		
Pulse width	t <sub>w</sub>	2.5±0.2	3.3	_	_	ns	LE "L"
		2.7	3.3	_	_		
		3.3±0.3	3.3	_	_		
		2.5±0.2	3.3	_	_	<del></del>	CLK "H" or "L"
		2.7	3.3	_	_	<del></del>	
		3.3±0.3	3.3	_	_	<del></del>	

### **Test Circuit**

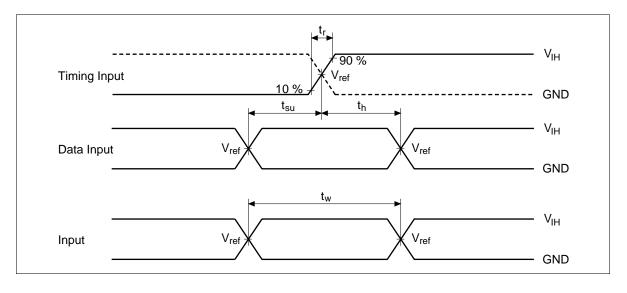


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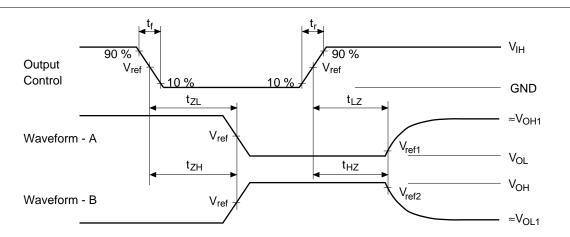
### Waveforms - 1



#### Waveforms - 2



#### Waveforms - 3



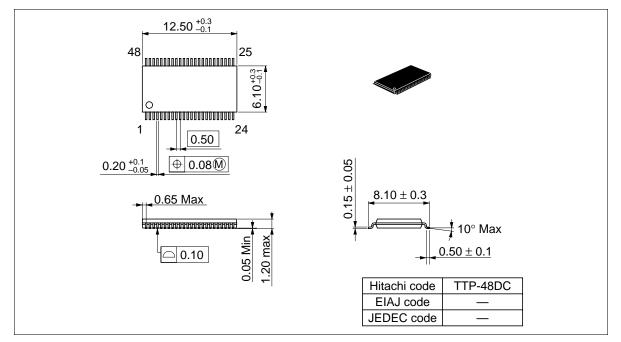
TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
$V_{IH}$	V <sub>CC</sub>	2.7 V
$V_{ref}$	1/2 V <sub>CC</sub>	1.5 V
$V_{ref1}$	V <sub>OL</sub> +0.15 V	$V_{OL}$ +0.3 $V$
V <sub>ref2</sub>	V <sub>OH</sub> -0.15 V	V <sub>OH</sub> -0.3 V
V <sub>OH1</sub>	V <sub>CC</sub>	3.0 V
V <sub>OL1</sub>	GND	GND

Notes:

- 1. All input pulses are supplied by generators having the following characteristics : PRR  $\leq$  10 MHz, Zo = 50  $\Omega$ ,  $t_{_{f}}\leq$  2.0 ns,  $t_{_{f}}\leq$  2.0 ns. (V $_{\text{CC}}$  = 2.5±0.2 V) PRR  $\leq$  10 MHz, Zo = 50  $\Omega$ ,  $t_{_{f}}\leq$  2.5 ns,  $t_{_{f}}\leq$  2.5 ns. (V $_{\text{CC}}$  = 2.7 V, 3.3±0.3 V)
- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

## **Package Dimensions**

Unit: mm



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# HTACHI

#### Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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#### For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park

Maidenhead Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Lower Cookham Road

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666

Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218

Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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